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## WHAT IS CLAIMED IS:

1. A semiconductor device comprising:  
a semiconductor substrate;  
source/drain regions provided in the semiconductor  
5 substrate;  
a gate insulating film provided on a channel  
region between the source/drain regions;  
a gate electrode provided on the gate insulating  
film;  
10 a conductive layer of a metal silicide provided on  
the gate electrode and the source/drain regions;  
an insulating film containing carbon provided on  
the semiconductor substrate so as to be in contact with  
at least the conductive layer; and  
15 an interlayer insulating film provided on the  
semiconductor substrate so as to cover the insulating  
film containing carbon.
2. The semiconductor device according to claim 1,  
wherein the insulating film containing carbon is mainly  
20 composed of a silicon nitride film.
3. The semiconductor device according to claim 2,  
wherein a content of the carbon is  $1 \times 10^{20} \text{ cm}^{-3}$  or  
more.
4. The semiconductor device according to claim 1,  
25 wherein a metal of the metal silicide is nickel.
5. The semiconductor device according to claim 1,  
wherein a metal of the meal silicide is at least one